6.12.2 MOSFET, Power, N-Channel

TRANSISTORS, MOSFET, N-CHANNEL, POWER, BASED ON TYPES STRH100N10, STRH40N6, STRH100N6 AND STRH8N10				**303E**
Procurement Specifications	Manufacturer	Nature of Approval	Supervising Authority	Initial Qualification Date
Generic ESCC 5000 Detail ESCC	STMicroectronics Rennes France	Qualification	CNES	Oct 2010
		Remarks		
5205/021, 5205/022, 5205/023, 5205/024				

Qualified range:

5205/021 & 5205/022: Variants 01 and 02 are qualified
5205/023 & 5205/024: Variant 01 is qualified

Package Types:TO-254AA, SMD.5 for STRH40N6 and STRH8N10

Maximum Ratings for 5205/021:

$V_{GS(th)}$	2 –4.5 min/max, I_D=1 mA
$r_{DS(on)}$ (m Ω):	35, V_{GS}=12V, I_D=24A
I_{DS} (A)	48, T_{case} (°C)= +25
V_{DS} (Vdc):	100 over Top , V_{GS}= 0 V
V_{GS} (Vdc):	± 20
P_{TOT}:	170 W at T_{case} ≤+25 C

Operating Temperature Range (°C): -55 to +150

6.12.3 MOSFET, Power, P-Channel

<table>
<tr><td colspan="4">TRANSISTORS, MOSFET,
P-CHANNEL, POWER,
TYPE STRH40P10 and STRH12P10</td><td>326D</td></tr>
<tr><td>Procurement Specifications</td><td>Manufacturer</td><td>Nature of Approval</td><td>Supervising Authority</td><td>Initial Qualification Date</td></tr>
<tr><td rowspan="2">Generic
ESCC 5000
Detail ESCC
5205/025
5205/029</td><td rowspan="2">ST Microelectronics
Rennes
France</td><td>Qualification</td><td>DLR</td><td>Mar 2013</td></tr>
<tr><td colspan="3">Remarks
These devices have a TID tested capability of 100kRAD(Si).</td></tr>
<tr><td colspan="5">Qualified range:

Variants 01 and 02 in 5205/025 are qualified.
Variants 01 and 02 in 5205/029 are qualified.</td></tr>
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